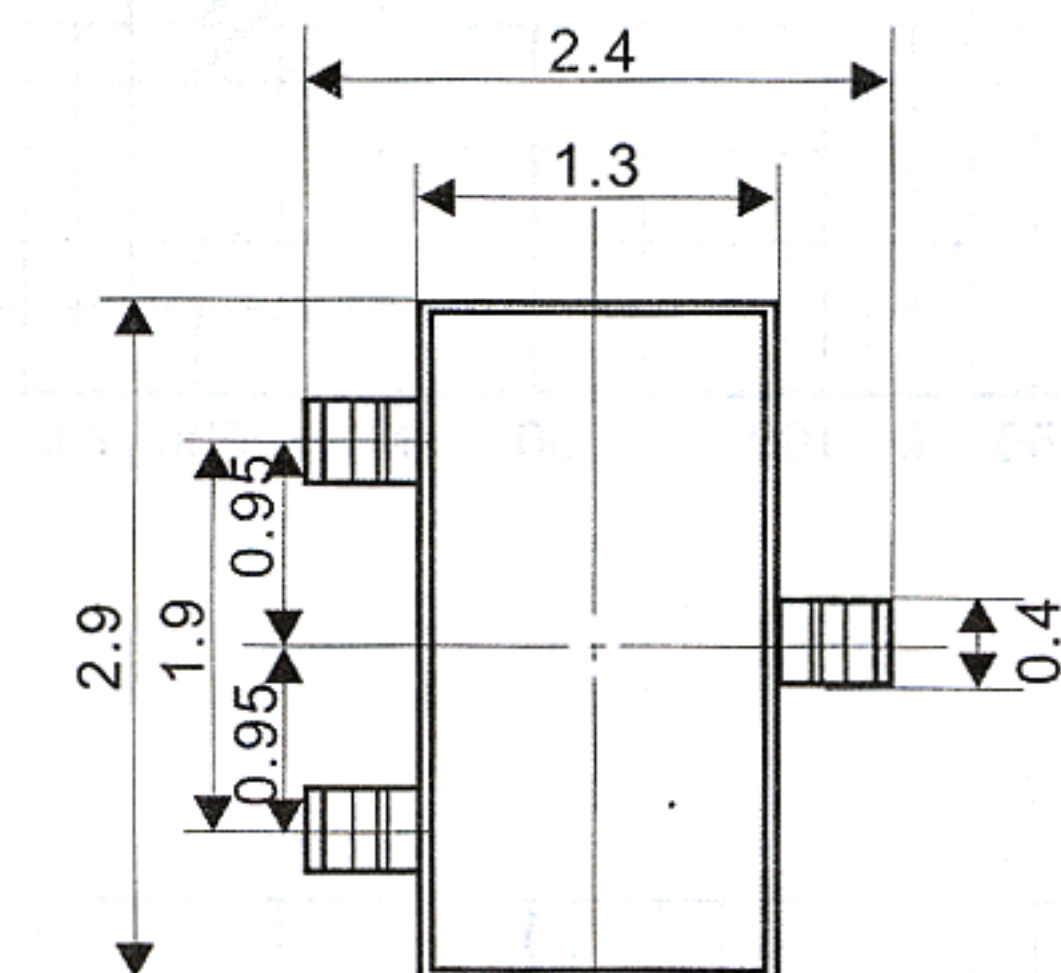
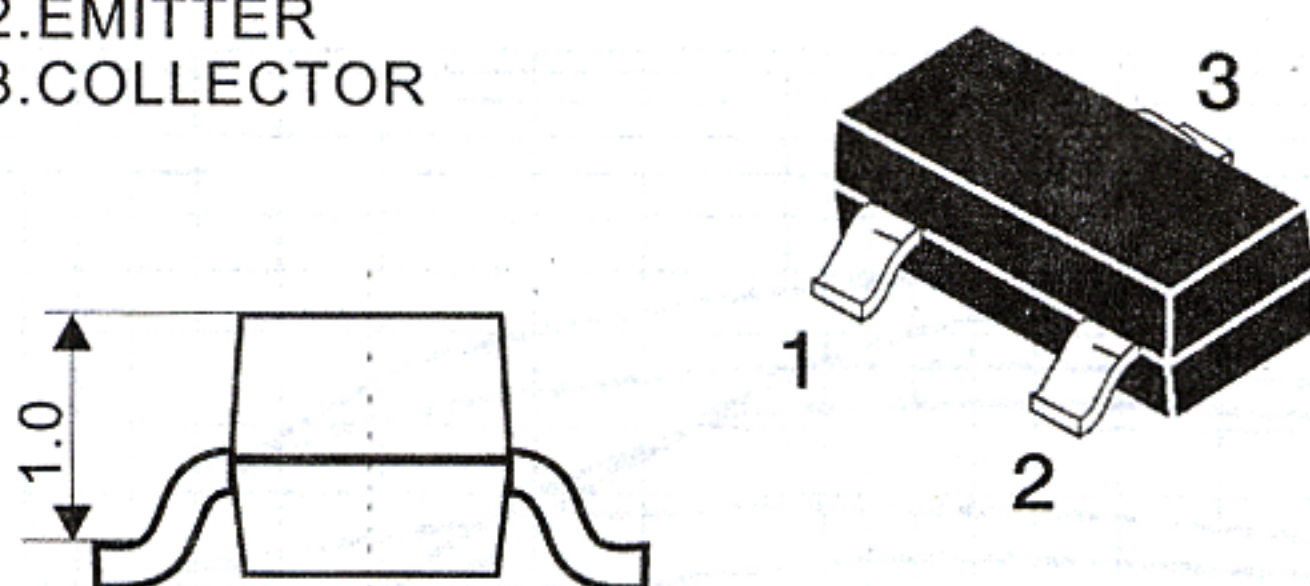


MMBT5401LT1 TRANSISTOR (PNP)

1.BASE
2.EMITTER
3.COLLECTOR



UNIT: mm

FEATURES

Power dissipation

P_{CM} : 0.3 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.6 A

Collector-base voltage

$V_{(BR)CBO}$: -160V

Operating and storage junction temperature range

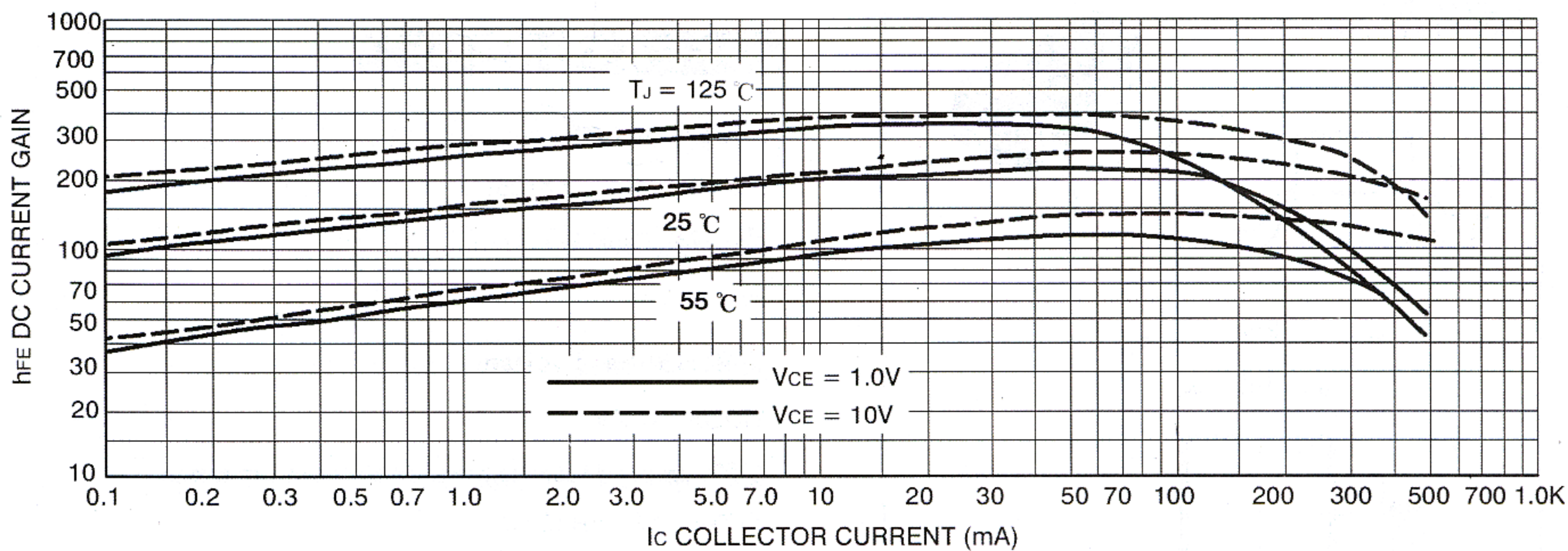
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

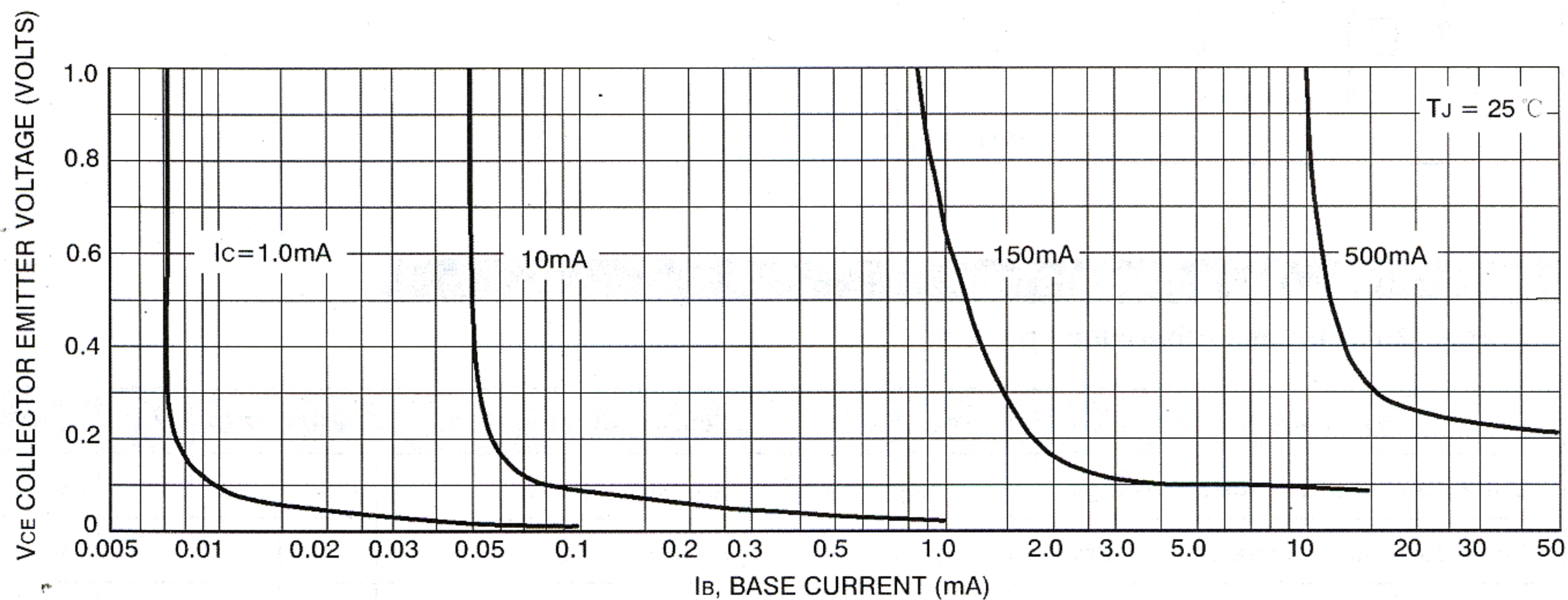
($T_{amp}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-160			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_B=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-120V, I_E=0$			-0.05	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4V, I_C=0mA$			-0.05	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-5V, I_C=-1mA$	80			
	$h_{FE(2)}$	$V_{CE}=-5V, I_C=-10mA$	100		200	
	$h_{FE(3)}$	$V_{CE}=-5V, I_C=-50mA$	50			
Collector-emitter saturation voltage	V_{CEsat}	$I_C=-500mA, I_B=-50mA$			-0.5	V
Base-emitter saturation voltage	V_{BEsat}	$I_C=-500mA, I_B=-50mA$			-1	V
Transition frequency	f_T	$V_{CE}=-20V, I_C=-50mA, f=100MHz$	100			MHz

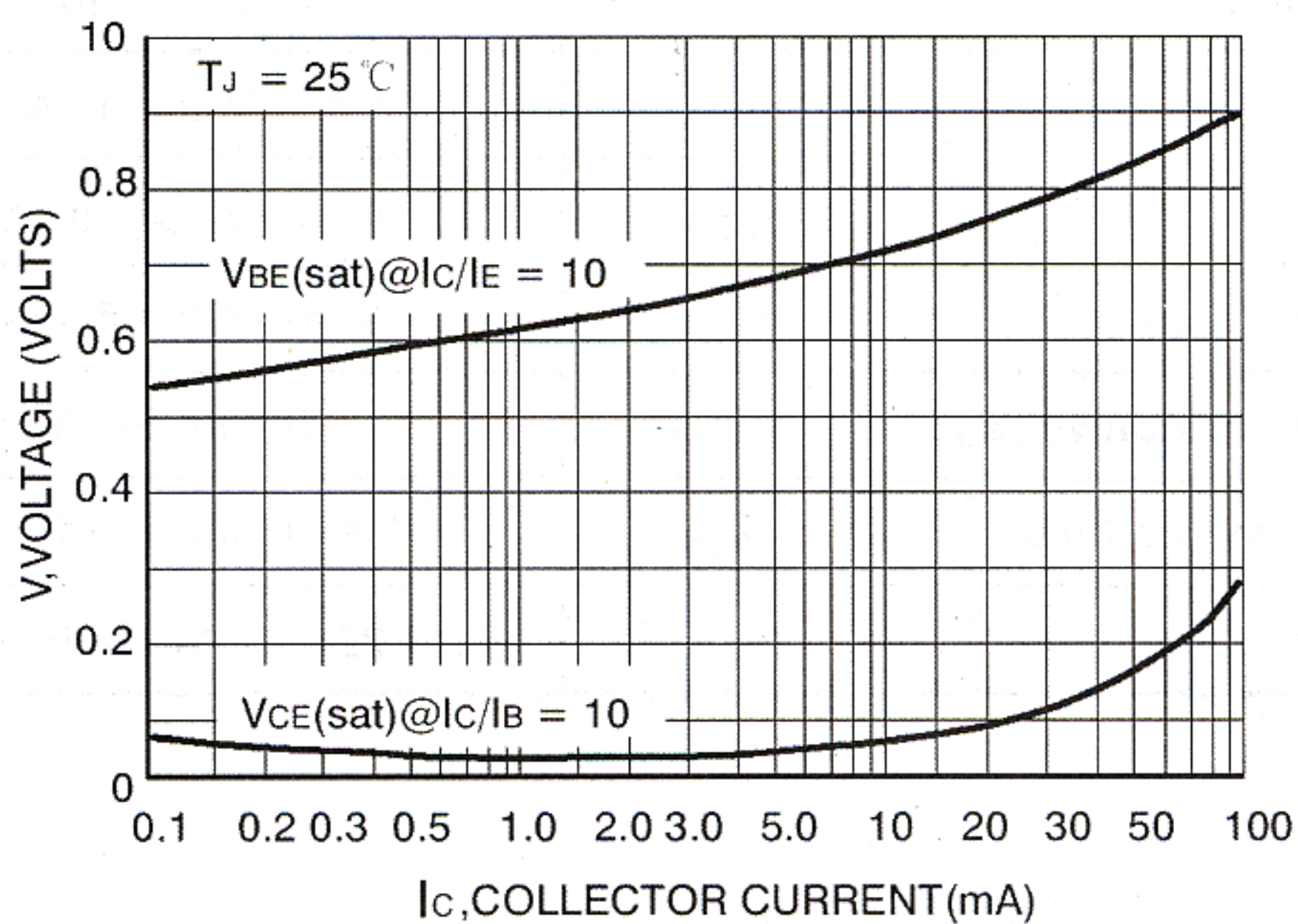
DEVICE MARKING : MMBT5401LT1=2L



DC Current Gain



Collector Saturation Region



"On" Voltages